

AMENDMENTS

In the Claims:

Please amend claim 1 as follows:

- Sub 31
1. (Amended) A nitride-based semiconductor light-emitting device comprising:
a silicon doped n-type GaN-based substrate; and
a semiconductor stacked-layer structure including a plurality of nitride-based semiconductor layers grown on said GaN-based substrate by vapor phase deposition,
said GaN-based substrate having an interface region contacting said semiconductor stacked-layer structure and said interface region containing oxygen atoms at concentration n in the range of $2 \times 10^{16} \leq n \leq 10^{22} \text{ cm}^{-3}$.

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Please add new claims 5-9 as follows:

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5. (New) A nitride-based semiconductor light-emitting device comprising:
a GaN-based substrate including a p-type impurity; and
a semiconductor stacked-layer structure including a plurality of nitride-based semiconductor layers grown on said GaN-based substrate by vapor phase deposition,
said GaN-based substrate having an interface region contacting said semiconductor stacked-layer structure and said interface region containing oxygen atoms at concentration n in the range of $2 \times 10^{16} \leq n \leq 10^{22} \text{ cm}^{-3}$.
6. (New) The nitride-based semiconductor light-emitting device according to claim 5 wherein said p-type impurity includes magnesium.
7. (New) The nitride-based semiconductor light-emitting device according to claim 5 wherein said GaN-based substrate contains chlorine.

8. (New) The nitride-based semiconductor light-emitting device according to claim 5 wherein said GaN-based substrate contains oxygen.

9. (New) The nitride-based semiconductor light-emitting device according to claim 5 wherein said plurality of nitride-based semiconductor layers included in said semiconductor stacked-layer structure include a layer contacting said GaN-based substrate, and said layer contacting said GaN-based substrate contains oxygen.
